

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

- Small surface mounting type
- High reliability

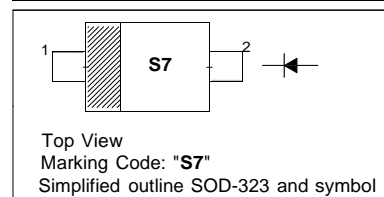
Applications

- Low current rectification

MARKING:S7

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	45	V
Reverse Voltage	V _R	40	V
Mean Rectifying Current	I _O	0.1	A
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I _{FSM}	1	A
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I _F = 100 mA at I _F = 10 mA	V _F	-	0.55	V
	V _F	-	0.34	V
Reverse Current at V _R = 10 V	I _R	-	30	μA
Capacitance Between Terminals at V _R = 10 V, f = 1 MHz	C _T	6	-	pF

Note: ESD sensitive product handling required.

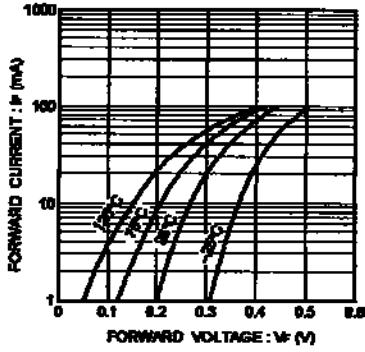


Fig. 1 Forward characteristics

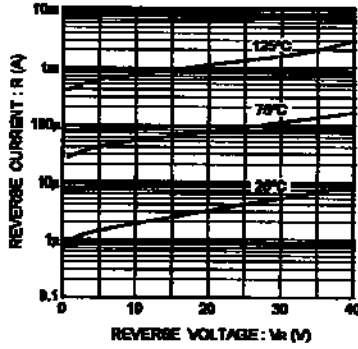


Fig. 2 Reverse characteristics

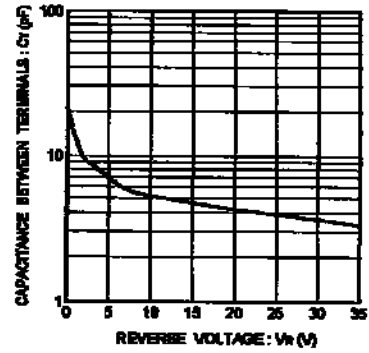


Fig. 3 Capacitance between terminals characteristics

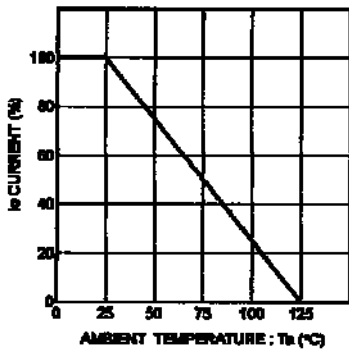


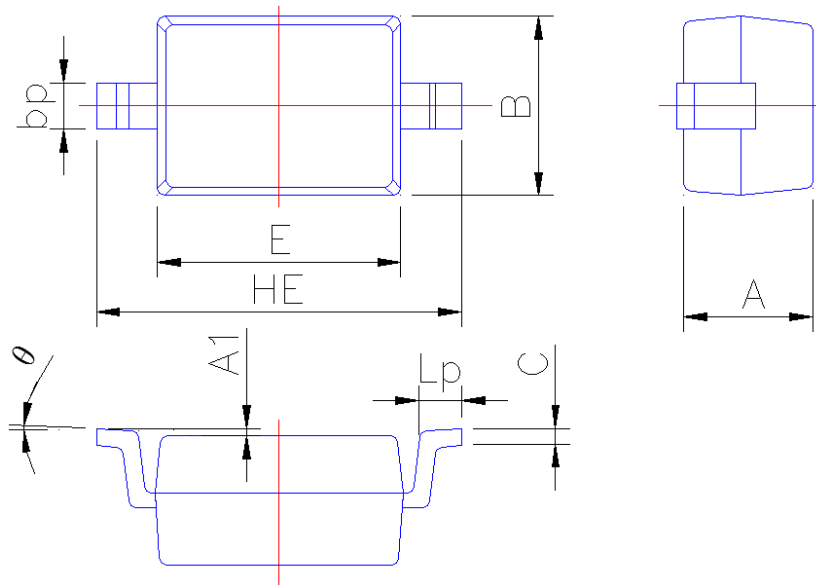
Fig. 4 Derating curve
(mounting on glass epoxy PCBs)



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°